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DS06-70105-1E

Semicustom Bi-CMOS

ASTRO-NT (for RF front-end LSI-Based on PLL, Analog Macro)

MB15G000 Series

■ DESCRIPTION

The ASTRO-NT* is a new technology to correspond to the demand of high performance RF LSI. The technology stands on a macro concept and create a custom LSI ideal for use in high frequency front-end circuit such as VCO, amplifier, mixer and I/Q modulator devices.

The chip can be built by combining macros, in accordance with user's demand function and characteristic. FUJITSU prepares standard RF macros. They are well finished in design and layout to fulfil good performance by function that a master slice method can not achive. It is possible to modify RF macro in response to user's demand.

This LSI series uses FUJITSU's latest BiCMOS process technology for low current consumption. In addition, many types of packages are available that makes it possible to find a proper size package for different circuit integration levels.

ASTRO-NT is ideal for applications with RF or IF signal, particularly mobile communication devices operating such as PDC, PHS, GSM, DCS, PCS and so on.

* Advanced Standard macro base Technology of PLL with RF system On LSI-New Technology

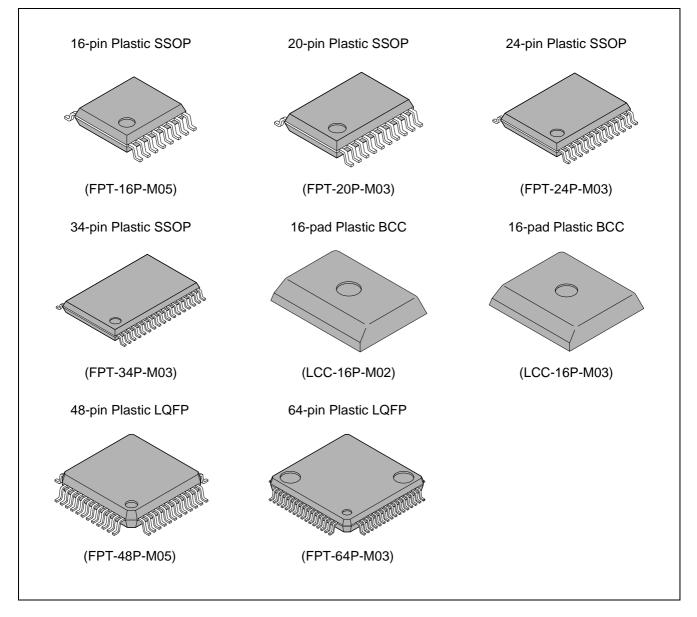
■ FEATURES

- High operating frequency: to 3.0 GHz (max)
- Supply voltage: 2.5 to 5.5 V
- Standard RF macro
- Low power consumption
- Package line up Many types of package are available.

SSOP-16, SSOP-20, SSOP-24P, SSOP-34, BCC-16, LQFP-48P, LQFP-64P,

- Operating temperature: -40 to +85°C
- Fujitsu's latest BiCMOS process technology

■ PACKAGES



■ MACRO DESCRIPTIONS

1. Prescaler

Divides the reference frequency by any given value and outputs the resulting frequency. Choice of two -modulus or fixed output mode.

2. PLL

Phase comparator

The phase comparator has a phase detection range of -2π to $+2\pi$, and is designed to eliminate blind spots in phase comparison by output of a margin-of-error signal to the charge pump even when the phase difference is zero. Phase comparator characteristics can also be tuned to the polarity of VCO.

Counters

The divide ratios of the comparator-side counter and reference-side counter can be either programmable or fixed.

Charge pump

The "H" level output voltage from the charge pump is determined by power supply voltage. Charge pump characteristics for the sending and receiving systems can be optimized for each specific application.

For example, when FM modulation is applied directly to the VCO signal, charge pump characteristic can be adjusted for lower speeds in order to reduce the sensitivity of the synthesizer loop so that output does not track the modulation.

• High speed lock-up circuit

This circuit is specially designed for faster lock-up speeds.

• Intermittent operation control circuit

This on-chip power-saving function reduces circuit current flow in standby status, enabling devices to operate with less power demand. A special circuit is built in to prevent excessive error signal from increasing lock-up delay during the transition from power-saving mode to operating mode.

• List of standard macros (Preliminary)

Туре	Vcc	lcc	Operating frequency	Prescaler divide ratio (M)	Comparator counter divide ratio (N)	Swallow counter divide ratio (A)	Reference counter divide ratio (R)
PLL1	3 V	1.0 mA*	0.5 GHz	8/9, 16/17	16 to 2047	0 to 127	8 to 16383
PLL2		2.0 mA*	1.2 GHz	32/33, 64/65			
PLL3		3.0 mA*	2.0 GHz				
PLL4		3.5 mA*	2.5 GHz				

Crystal oscillator input frequency: Up to 32 MHz

Standby mode current demand: 10 μ A(Max.)

* : Target spec.

Note: Refer to macro specification book.

3. RF Analog Macro List (Preliminary)

Circuit	Function	Voltage	Current	Application example	
	900 MHz QMOD + AGC		29.5 mA	PDC	
	1.9 GHz Doubler + MOD + UpCONV (IF = 233 MHz)+AGC			28.5 mA	PHS
QMOD/QDEM	0.9, 1.9 GHz Doubler + MOD UpCONV IF = 300 to 450 MHz			27.0 mA	GSM/DCS,PCS
	130 MHz Shifter QMOD		8.0 mA	CDMA	
	85 MHz Shifter + QDEM	3.0 V	8.2 mA	CDMA	
	Lo = 250 MHz, IF = 10.8 MHz 2 nd Mixer		3.7 mA	PHS	
2 nd Mixer	$L_0 = 130 \text{ MHz}$, IF = 450 kHz 2 nd Mixer		2.6 mA	PDC	
	400 MHz IFAMP + 2 nd MIX		5.0 mA	GSM/DCS,PCS	
	1.2 to 1.6 GHz Local Buffer AMP		5.0 mA	GSM/DCS,PCS	
	400 MHz VCO + VCO Buffer		5.0 mA	GSM/DCS,PCS	
Buf AMP/VCO	260 MHz VCO (Tx)		3.5 mA	CDMA	
	170 MHz VCO (Rx)		3.5 mA	CDMA	
	450 kHz LimAMP/RSSI		2.3 mA	PDC	
Lim AMP/RSSI	10.8 MHz LimAMP/RSSI 10.8 MHz LimAMP/RSSI		2.3 mA	PHS	
1 st Mixer	Lo = 718 MHz, IF = 130 MHz 1 st Mixer		4.5 mA	PDC	
Offset Mixer	Lo = 718 MHz, RF = 850 MHz Tx-Mixe		6.0 mA	PDC	
RF AMP	850 MHz RF-AMP		2.5 mA	PDC	
AGC AMP	130 MHz AGC	Gp = 40 dB Gp = -55 dB	3.6 V	19 mA 4.9 mA	CDMA

Note: Circuit format and other details can be adjusted to meet customer requirements.

Refer to macro specification book.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Ra	Unit		
Falameter	Symbol	Min.	Max.	Unit	
Power supply voltage *	Vcc	-0.5	6.0	V	
Input voltage *	Vin	-0.5	Vcc + 0.5	V	
Output current	lout	-10	10	mA	
Storage temperature	Tstg	-55	+125	°C	

* : Voltage values are based on GND = 0 V

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value			Unit
Farameter		Min.	Тур.	Max.	Onic
Power supply voltage *1	Vcc *2	2.5	—	5.5	V
Fower supply voltage	GND	—	0	_	V
Operating temperature	Та	-40	—	+85	°C

*1: Voltage values are based on GND = 0 V

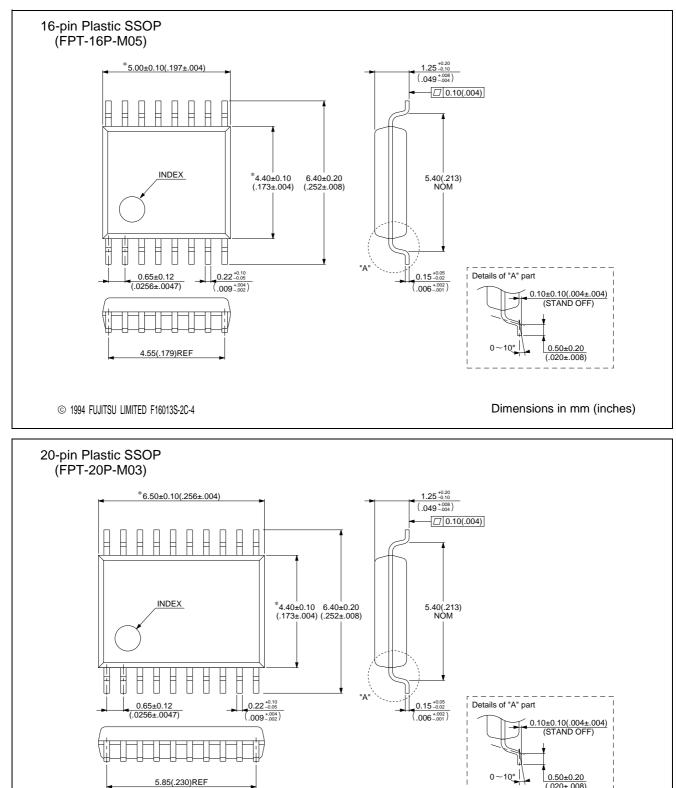
*2: The range of operating voltage should be defined depends on circuit configuration.

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

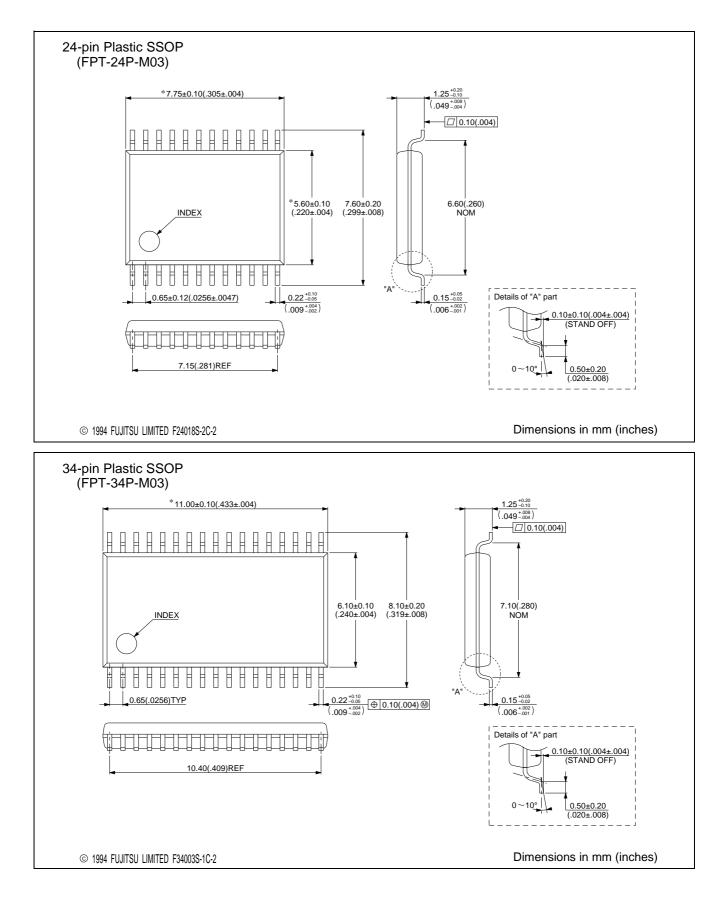
Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

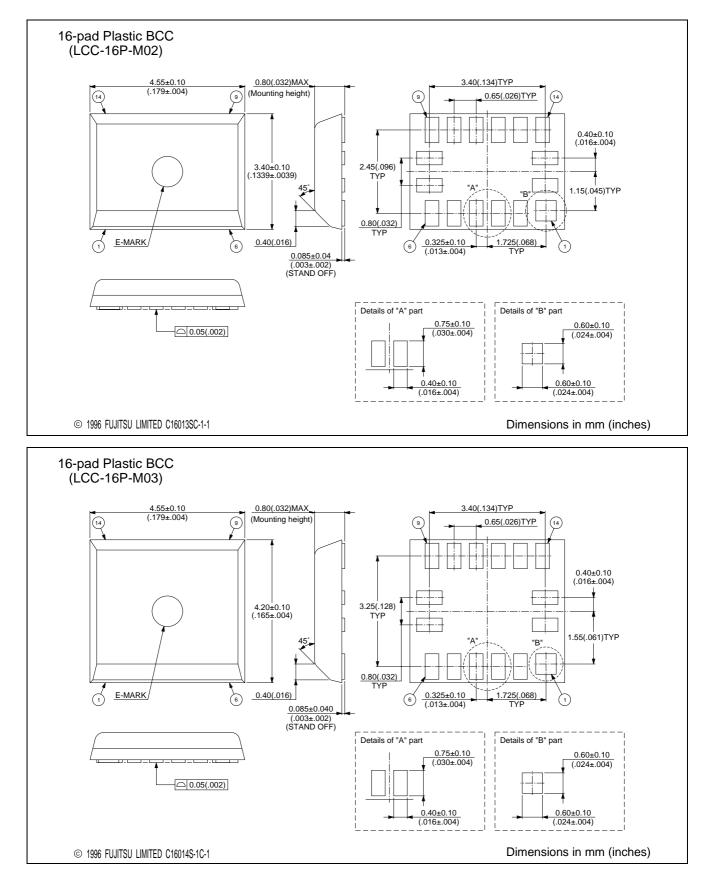
No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

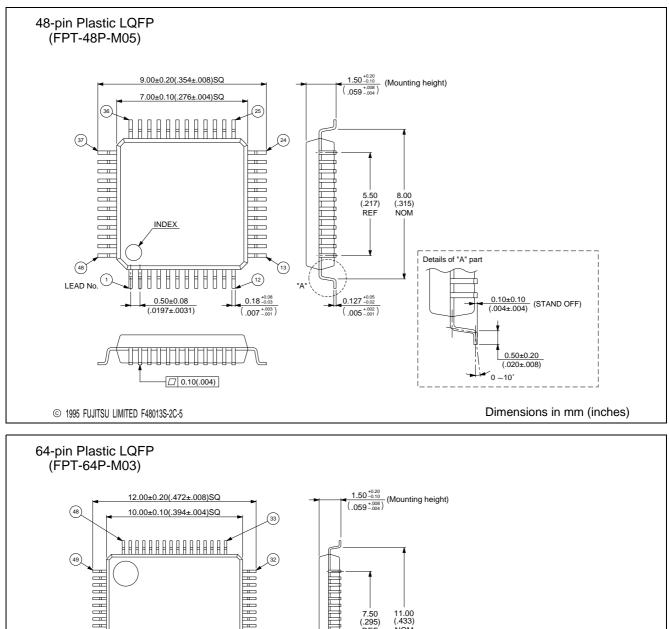
■ PACKAGE DIMENSIONS

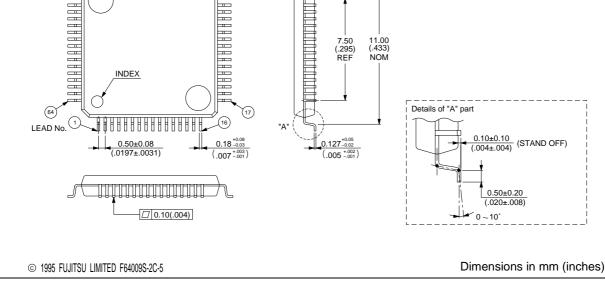


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